

OPERATIONAL AMPLIFIER 741

T-07-27 T-27-29

T-58-11-13

PACKAGE TO-99 (8 LEADS)

T-11-21

Absolute Maximum Rating Stg. Temp. -65°C; to 150°C Operating temp. 0°C to 70°C

PARAMETER	CONDITION	VALUE			UNIT
		Min	Typ	Max	
Supply Voltage				±18	Volts
Internal power dissipation	TA upto 70°C			500	mw
Electrical Characteristic @ VS =+15 V, TA=25°C					
Input Offset Voltage	RS ≤ 10 K ohm		2	6	mV
Input Offset Current			20	200	nA
CMRR	RS ≤ 10 K ohms	70	90		dB
Large Signal	RL ≥ 2 K ohms;	20,000	200,000		
Voltage Gain	Vout = ±10V				
Slew Rate	RL ≤ 2 K ohms		0.5		V/μ sec.

VOLTAGE REGULATOR 723

PACKAGE TO-100 (10 LEADS)

Absolute Maximum Rating : Stg. Temp. -65°C to 150°C; Operating Temp. 0°C to 70°C

Continuous Voltage	From V+ to V-		40		Volts
Current From Vout			150		mA
Internal power dissipation	TA upto 25°C		800		mW
Electrical Characteristic: TA=25°C					
Line Regulation	V in=12 V to 40 V		0.1	0.5	%Vout
Load Regulation	IL=1 mA to 50 mA		0.03	0.2	%Vout
Reference Voltage		6.80	7.15	7.50	Volts
Temp. Coefficient of	0°C ≤ TA ≤ 70°C			0.015	%/°C
Output Voltage					

Device	VCEO	VCBO	VEBO	hFE at bias	IC	VCE	hFE1/hFE2	ICM	PTA	ICBO	VCE(sat)	Package
	Volts	Volts	Volts	mA	mA	Volts	(min)	mA	mW	μA	Volts	
	min	min	min	min/max				max	max	typ	typ	

DARLINGTON PAIR TRANSISTOR

(Low leakage, small signal intended for very high gain, high impedance and low noise applications)

CIL 997	40	40	10	1000/	10	10		500	400	0.02	0.8	TO-105
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DIODES

Device	PIV	VF at IF	IR at VR	PTA	IFM	CT at VT	Package
	Volts	Volts	mA	μA	Volts	mW	PF
							Volts

NOISE LIMITER DIODES

(sine wave to square wave conversion—in both direction—for industrial applications)

CD 80		1.0	200		500	400	TO-105 Mod.
CD 81		1.0	100		500	400	TO-105 "

STABISTOR DIODES

(Low voltage, for Voltage stabilizers and other industrial and general purpose applications)

CA 301	5	1.0	20	1.0	2	200	DO-7 "
U1	5	1.4	10	1.0	7	400	TO-106 Mod

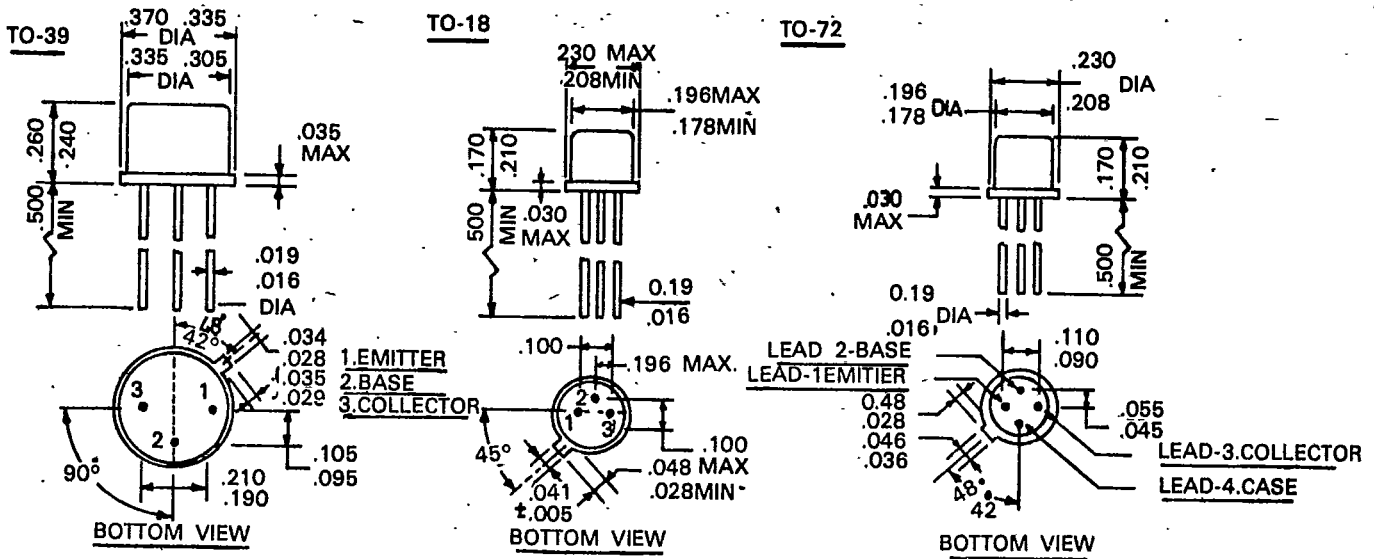
VARICAP DIODES

(Varactor or variable capacitance, primarily designed for use in electronically tunable resonant circuits, in VHF frequency range)

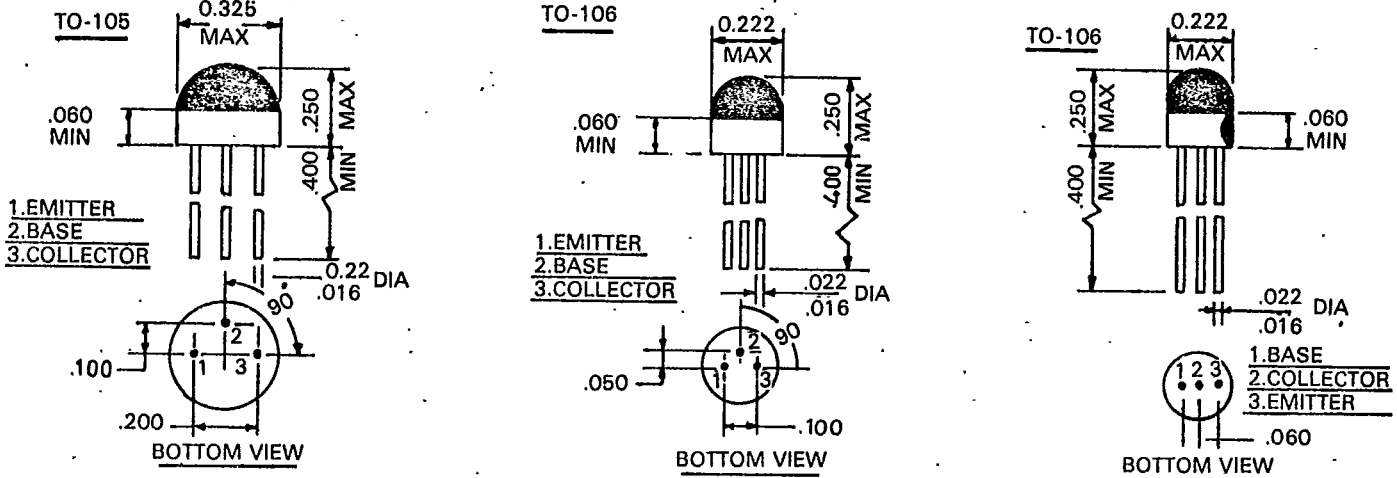
CD 90		100	20	200		20/30	4	TO-106 Mod
CD 91		100	20	200		15/25	4	TO-106 "
CT 90		100	15	200		15/25	4	DO-35 "
CD 102		100	20	200		20/40	4	TO-106 Mod

ALL DIMENSIONS IN INCHES

PACKAGE OUTLINES



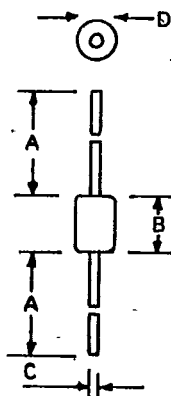
For transistor BF 167, 173 in TO-72 Package Base & Emitter leads get interchanged.



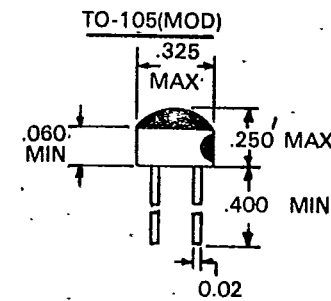
Note; For HF. transistor TO-106 Package 1. Base 2. Emitter and 3. Collector

TYPICAL DIMENSIONS

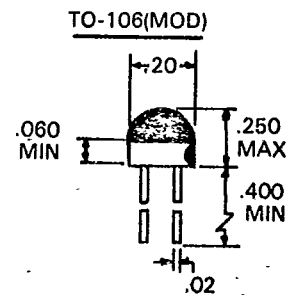
Dim	Package			
	DO-7	DO-35	DO-41	DO-34
A	1.100	1.100	1.100	1.100
B	0.230	0.140	0.150	0.104
C	0.020	0.020	0.032	0.020
D	0.096	0.070	0.94	0.056



LEAD ADJACENT TO DOT OR BAND-IS CATHODE

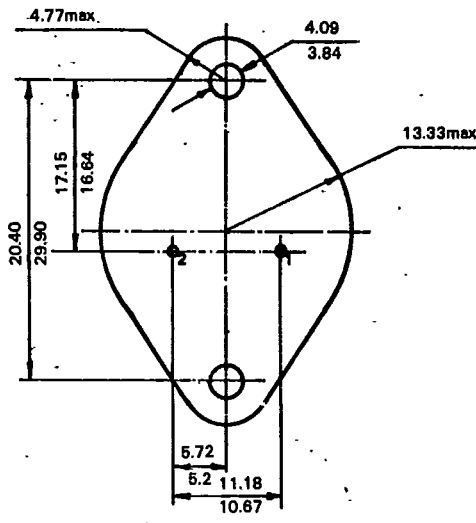
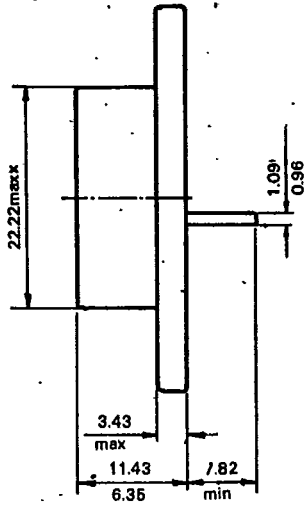


LEAD ADJACENT TO DOT IS CATHODE



LEAD ADJACENT TO DOT-IS CATHODE

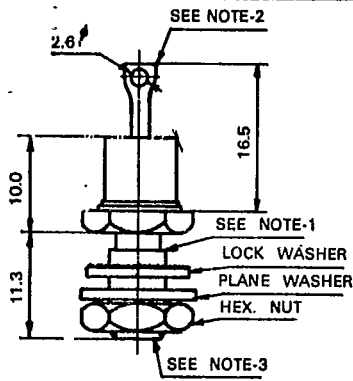
PACKAGE OUTLINES



TO-204AA

Pin Configuration: 1:Base
2:Emitter
Body : Collector

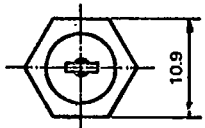
ALL DIMENSIONS IN M.M.



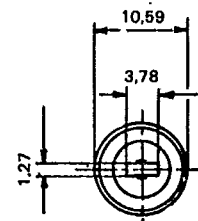
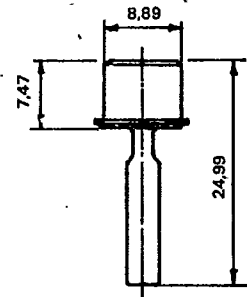
NOTES:

1. Threads to extend to within 2—1/2 threads of seating plane.
2. Angular orientation undefined.
3. lo-32 UNF-2A maximum pitch dia shall be (1687" 4.29 mm)

(All dimensions in mm)

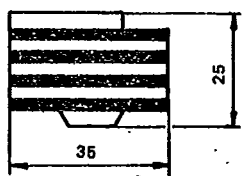
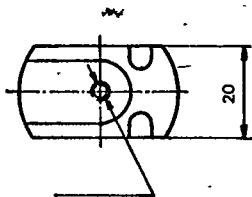


DO-4

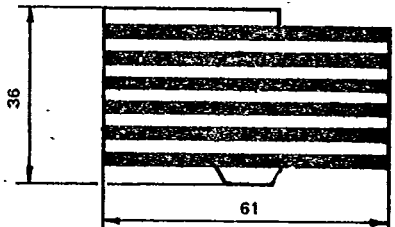
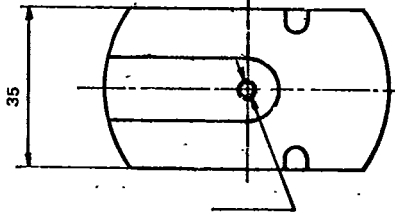


DO-21

HEAT SINK:



K 6 (3,6 AMP. DIODES)



K 12 (12 AMP. DIODES)

PACKAGE OUTLINES

FOR TO-92 AND TO 237 PACKAGE PIN CONFIGURATION FROM LEFT TO RIGHT IS COLLECTOR-BASE-EMITTER, KEEPING FLAT FACE IN FRONT AND LEADS POINTING DOWNWARDS.

